

Abstract of the Disclosure

A method for fabricating a semiconductor device, wherein a multi-layered hard mask layer having a stacked structure of nitride film/oxide film/nitride film is disclosed. The method for fabricating a semiconductor device comprises the steps of: forming a gate insulating film and a conductive layer for gate electrode; forming a multi-layered hard mask layer on the conductive layer, wherein each layer of the multi-layered hard mask layer is formed of materials different from one another; etching the structure to form a stacked structure of a gate insulating film pattern, a gate electrode and a hard mask layer pattern; forming an insulating film spacer; forming an interlayer insulating film on the entire surface; etching the interlayer insulating film to form a landing plug contact hole; forming a conductive layer for landing plug on the entire surface; and planarizing the conductive layer for a landing plug to form a landing plug.